

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Hisashi OHTANI et al.

Serial No. 08/807,737

Filed: February 27, 1997

For: METHOD FOR MANUFACTURING
SEMICONDUCTOR DEVICE

)
) Group Art Unit: 2829
) Examiner: Evan T. PERT
)
) Date: March 3, 2003

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CERTIFICATE OF MAILING

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Deborah Movahhedi
Deborah Movahhedi

#52/
MAET
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AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed October 2, 2002, please consider the following amendments and remarks in connection with the above-identified application.

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IN THE CLAIMS:

Please amend claims 60, 61, 73, and 84 as follows:

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60. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

21 forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate by using a CVD system;

forming a semiconductor film comprising amorphous silicon on said silicon nitride film;

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02 FC:1201

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